

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. MICRON.281A	APPLICATION NO. Not Yet Known 10/801,993
	APPLICANT Chandra V. Mouli	
	FILING DATE Herewith 03/16/2004	GROUP Not Yet Known 2822

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
TYT	1	4,199,773	04/22/80	Goodman et al.	—	—	—
	2	5,024,965	06/18/91	Chang et al.	—	—	—
	3	5,164,805	11/17/92	Lee	—	—	—
	4	5,166,765	11/24/92	Lee et al.	—	—	—
	5	5,231,045	07/27/93	Miura et al.	—	—	—
	6	5,315,144	05/24/94	Cherne	—	—	—
	7	5,501,993	03/26/96	Borland	—	—	—
	8	5,599,728	02/04/97	Hu et al.	—	—	—
	9	5,614,433	03/25/97	Mandelman	—	—	—
	10	5,942,781	08/24/99	Burr et al.	—	—	—
	11	6,037,617	03/14/00	Kumagai	—	—	—
	12	6,268,630	07/31/01	Schwank et al.	—	—	—
	13	6,503,783	01/07/03	Mouli	—	—	—

FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
TYT	14	Park et al., "Dopant Redistribution in SOI during RTA: A Study on Doping in Scaled-down Si Layers", <i>IEEE</i> , 1999, pp 14.2.1 through 14.2.4.
TYT	15	"A.1.3.2 Spurious Effects in Sub-Micron MOSFETs", http://www.iue.tuwien.ac.at/diss/schrom/diss/node90.html
TYT	16	"2.7.2 Threshold Control", http://www.iue.tuwien.ac.at/diss/schrom/diss/node26.html
TYT	17	"Random discrete dopant fluctuation; Ultra-thin channel SOI", http://www.research.ibm.com/0.1um/pwong.html

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EXAMINER	THANH TRAN	DATE CONSIDERED	11/18/04
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.			